

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L17	150270	(float\$6 adj gate) or ((charge or electron) near5 (stor\$6 or trap\$6 or strap))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 19:44
L18	29495	17 and ((flash or SONOS or nonvolatile or volatile) adj memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 19:43
L19	6801	18 and (((float\$6 adj gate) or ((charge or electron) near5 (stor\$6 or trap\$6 or strap))) same (sidewall or (side adj wall) or spacer or trench or opening))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 19:45
L20	4641	19 and (remov\$6 near15 (mask\$6 or hardmask or nitride or oxynitride or pattern\$6 or dielectric or oxide or tunnel\$6))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 19:47
L21	4627	20 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 19:47
L22	4227	21 and (source or drain or sourc?drain or S?D)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 19:48
L23	4225	22 and (substrate or wafer or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 19:48